

IN THE ABSTRACT:

Please amend the Abstract as follows:

In a CMP process for polishing copper and a barrier metal formed on a substrate to form a buried copper interconnect, a polishing pad is subjected to dressing under a dressing pressure of 29g/cm^2 so that the surface roughness of the polishing pad becomes $[[3\mu\text{m}]]$ $6\mu\text{m}$ to $[[5\mu\text{m}]]$ $8\mu\text{m}$ inclusive. Thereby, dishing of the copper interconnect can be reduced as compared with a known method without reducing the removal rate of the copper and barrier metal.